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a wiring layer formed on the insulation layer,
the electrodes of the semiconductor chip and the wiring layer
being connected to each other via connection members disposed in
the insulation layer wherein said connection members extend in a
direction perpendicular to the semiconductor chip, have a
longitudinal shape, and have an area of contact with the wiring
layer that is less than an area of contact with an electrode.

7. (Amended) A method for fabricating a semiconductor device
comprising the steps of:

preparing a wafer including a plurality of semiconductor chips
with electrodes formed thereon;

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forming connection members on the electrodes of the respective
semiconductor chips, the connection members extending in a direction
perpendicular to the semiconductor chips and having a longitudinal
shape and an area of contact with a herein later identified wiring
layer that is less than an area of contact with an electrode;

forming an insulation layer in a thickness to cover the
connection members on the surfaces of the respective semiconductor
chips where the electrodes of the semiconductor chips are formed;

polishing the insulation layer to expose the connection members;

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forming an electroless plated layer on the insulation layer; and
forming, with the electroless plated layer as a feeder layer of electric current, an electrolytic plated layer on the electroless plated layer selectively only in regions for a wiring layer;

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cont. etching off the electroless plated layer except regions of the electroless plated layer corresponding to the electrolytic plated layer to form the wiring layer including the electroless plated layer and the electrolytic plated layer; and

severing the wafer into the respective semiconductor chips to fabricate the semiconductor device.

Please add the following new claims:

16. (New) The semiconductor device according to claim 2, wherein the wire bumps are Au wire bumps.

A3
17. (New) The method for fabricating a semiconductor device according to claim 9, wherein the wire bumps are Au wire bumps.
